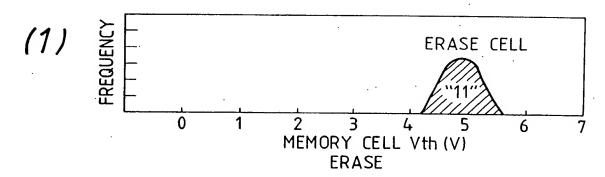
FIG. 1

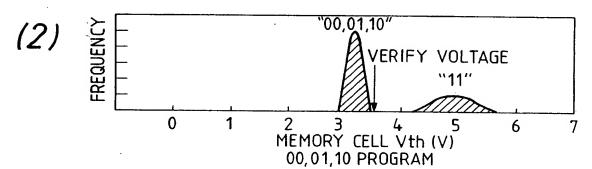
(1)	1ST DATA		0 0	1	0 1	1 1
	2-BIT DATA			'01'	10'	.11.
(2)	1ST OPER	ATION (a NAND b) ATION (NOT b)	1	1	1	0
	3RD OPER	· · · · · · · · · · · · · · · · · · ·	1	0	. 0	0
	NO. OF 1		3 .	2	1	0
(3)	DATA	THRESHOLD VALUE				
e. 1	'00' '01' '10' '11'	V0 - 3Va V0 - 2Va V0 - Va V0 (=ERASE LEV	EL)			

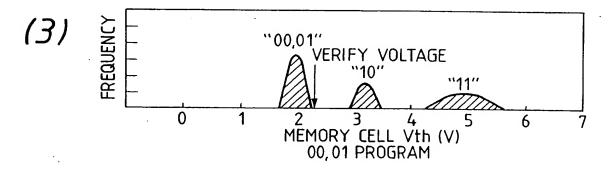
FIG. 2

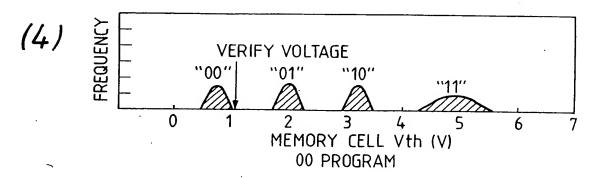
	•							
	С	0	0	0	1	(READ	LEVEL:	HIGHT)
	d	0	. 0	1	1	(READ	LEVEL:	MEDIUM)
	f 	0	1	1	1		LEVEL:	•
	d NAND f	1	0	1	1			
(d NAND	f) NAND c	0	1	0	1	= a		
	d	0	0	1	1	= b		

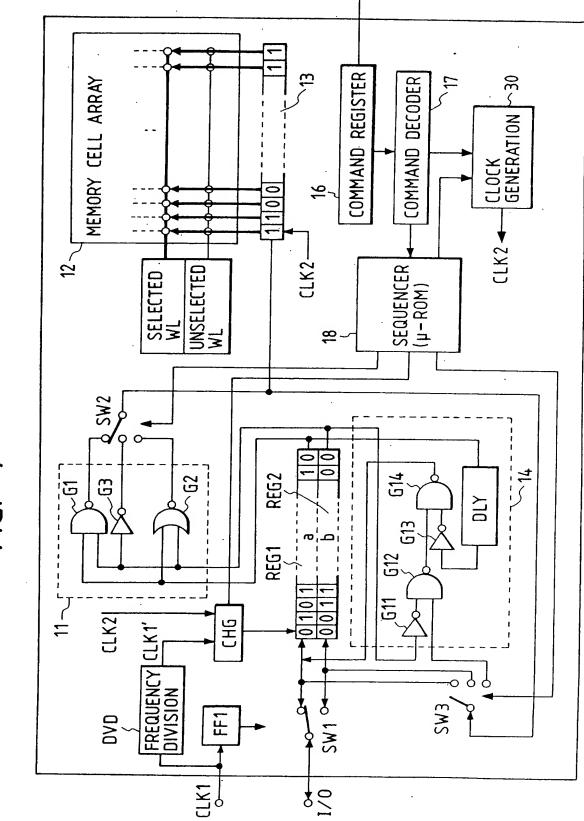






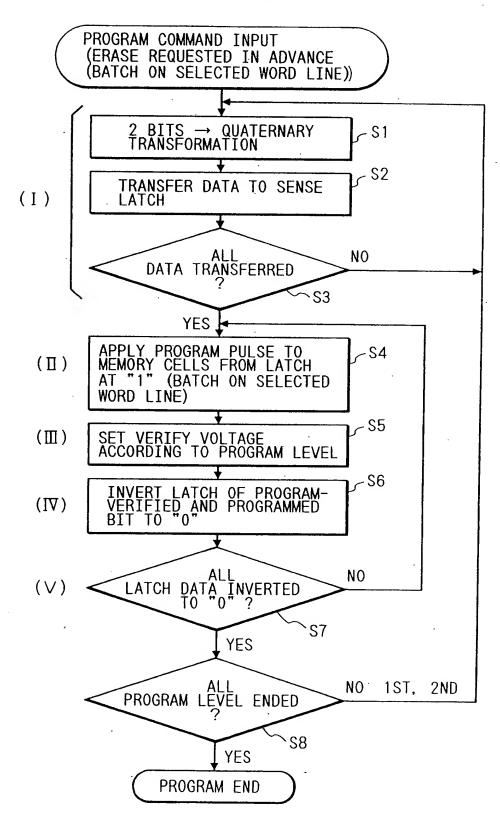


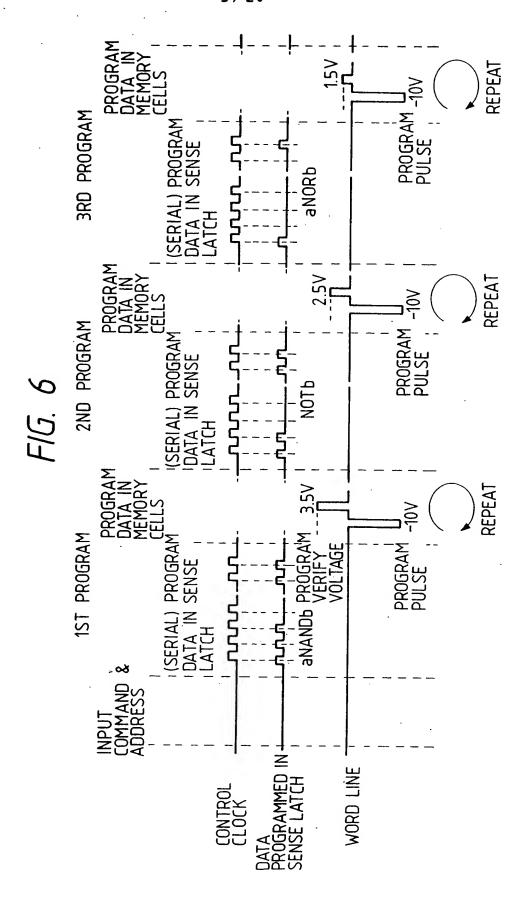




F1G. 4

FIG. 5





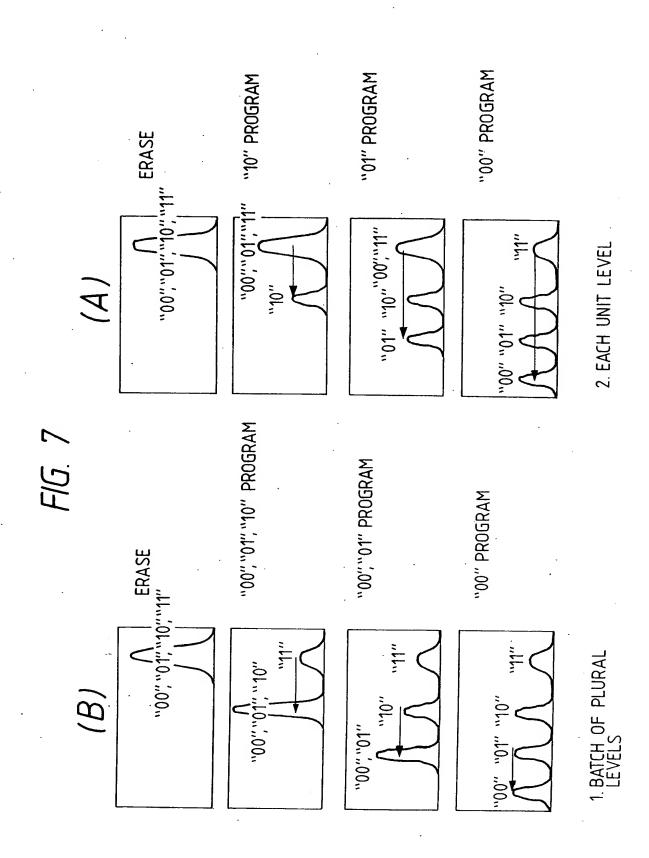
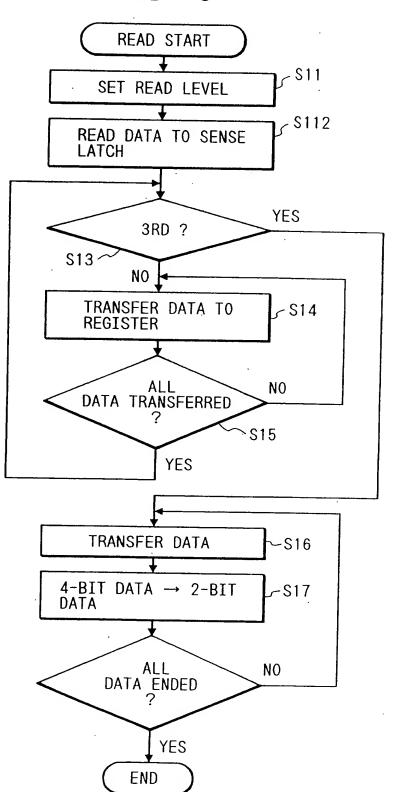
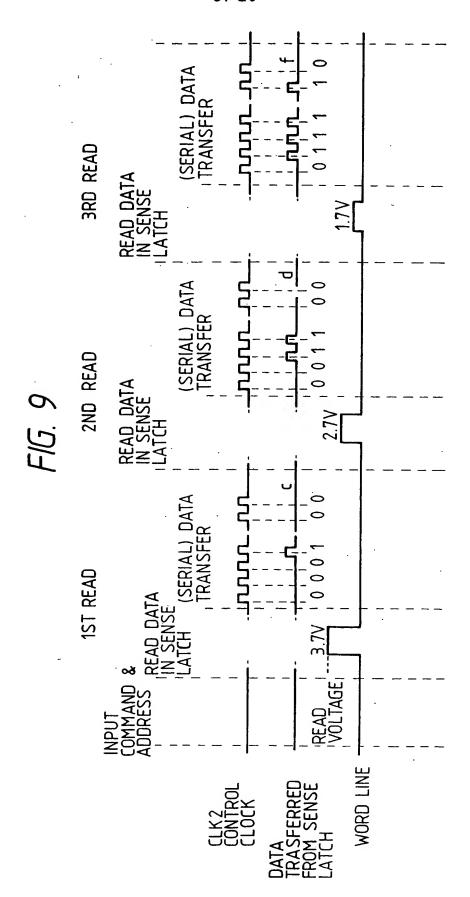
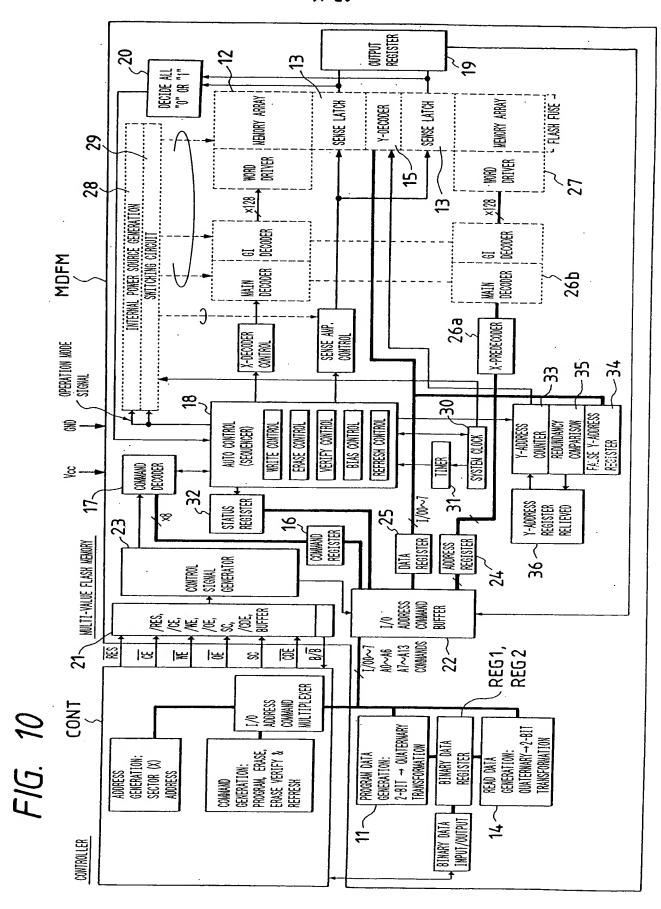


FIG. 8







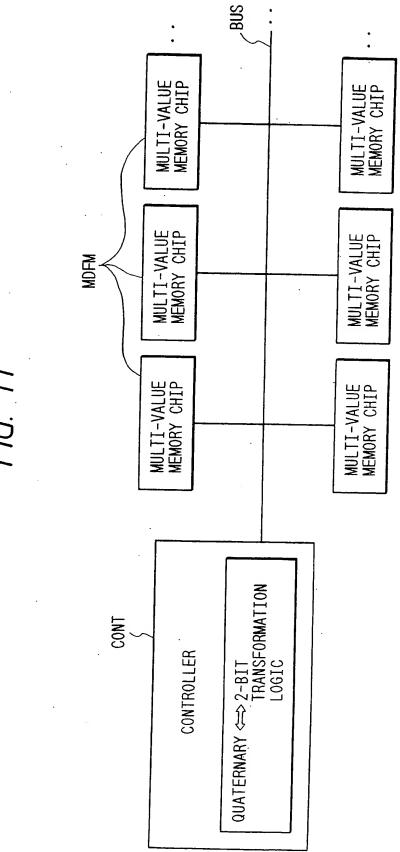


FIG. 12

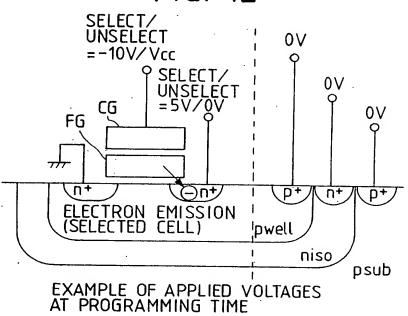


FIG. 13

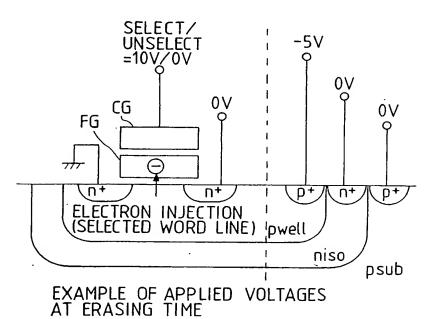
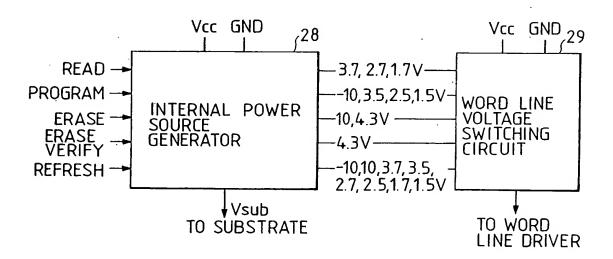
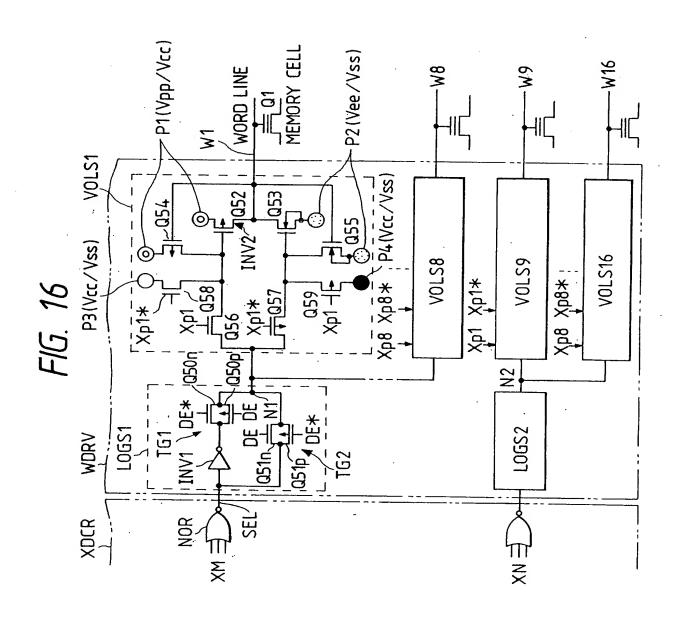


FIG. 14 SELECT/ UNSELECT = 3.7,2.7,1.7V/0V **0V** SELECT/ UNSELECT =1.5V/0V 0V CĺQ 0V FG // (p+/ <u>(n+</u> P+ n+ **READ CURRENT** pwell niso psub EXAMPLE OF APPLIED VOLTAGES AT READING TIME

FIG. 15





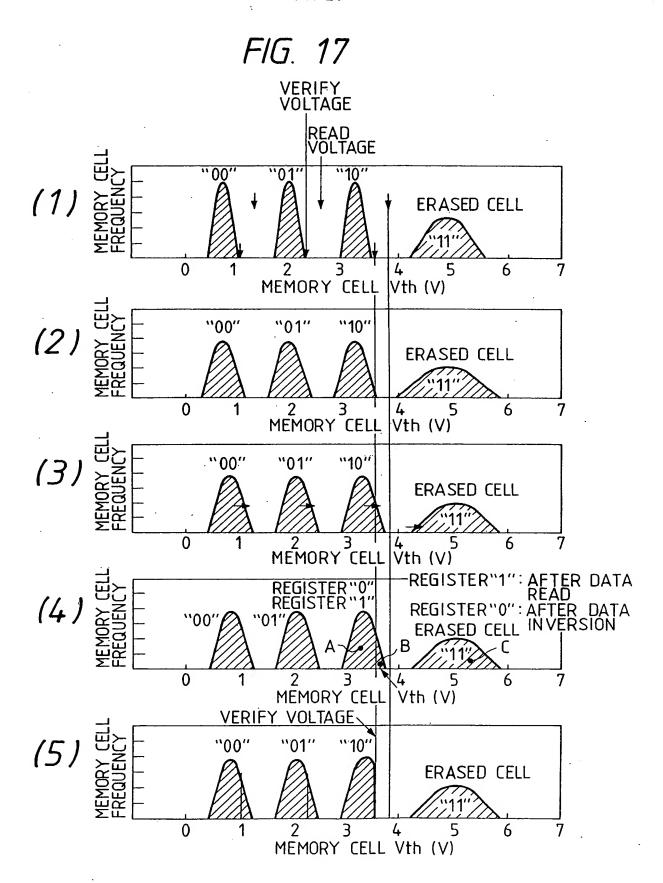
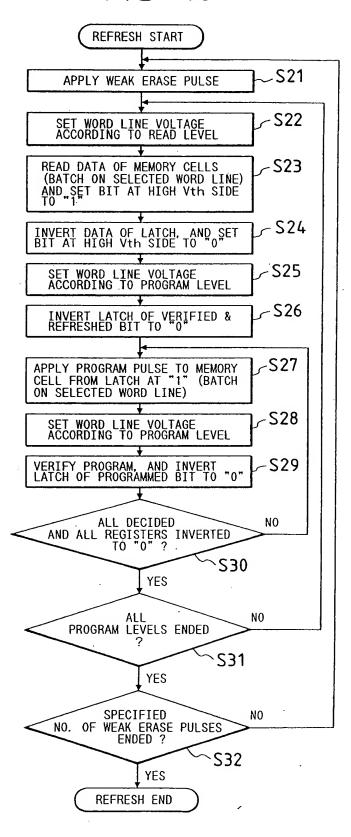


FIG. 18



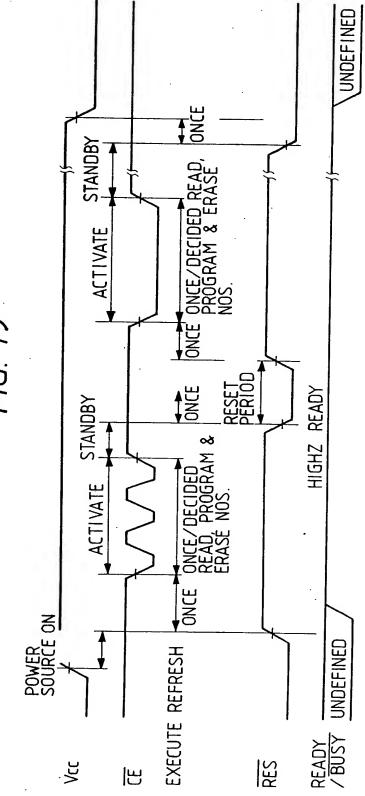


FIG 19

